

ABSTRACT

A method of fabricating polysilicon lines and polysilicon gates, the method of including: providing a substrate; forming a dielectric layer on a top surface of the substrate; forming a polysilicon layer on a top surface of the dielectric layer; implanting the polysilicon layer with N-dopant species, the N-dopant species about contained within the polysilicon layer; implanting the polysilicon layer with a nitrogen containing species, the nitrogen containing species essentially contained within the polysilicon layer.